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ATTY. DOCKET NO.

160-399

DIVISIONAL OF SERIAL NO.

10/229,067

APPLICANT

Nakamura et al

FILING DATE

November 24, 2003

GROUP

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,684,309	11/1997	McIntosh et al	257	14	
	4,862,471	8/1989	Pankove	372	45	
	5,646,953	7/1997	Naito et al	372	46	
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					YES	NO
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6-21511	1/1994	Japan				
3-290984	4/1990	Japan				
4-218994	8/1992	Japan				
7-074431	3/1995	Japan				X
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**OTHER DOCUMENTS (including Auth r, Titl , Date, Pertinent pages, tc.)**

*Examiner	Date Considered
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	Narukawa et al Phys. Rev. B Vol. 55, No. 4, pp R1938-1941-1/97 Recombination dynamics of localized excitons in $\text{In}_{0.20}\text{Ga}_{0.80}\text{N-In}_{0.05}\text{Ga}_{0.95}\text{N}$ multiple quantum wells
	Narukawa et al Appl. Phys. Lett. 70 (8), pp 981-983, 2/1997 Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm
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	Appl. Phys. Lett., 38 (11) June 1981 pp 835-837

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